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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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2SC3380

Silicon NPN Triple Diffused



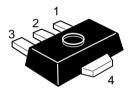
ADE-208-1082A (Z) 2nd. Edition Mar. 2001

Application

- High frequency high voltage amplifier
- High voltage switch

Outline

UPAK



- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector (Flange)

Note: Marking is "AS".

2SC3380

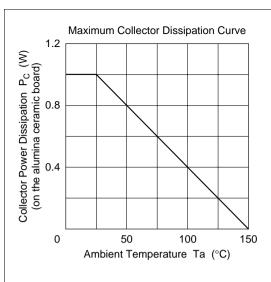
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

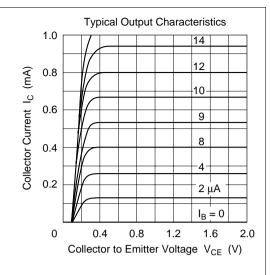
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	300	V
Collector to emitter voltage	V _{CEO}	300	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I _c	100	mA
Collector power dissipation	P _c *1	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

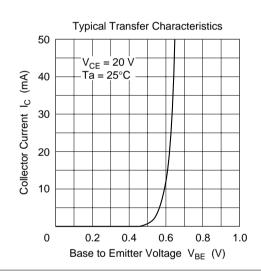
Note: 1. Value on the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

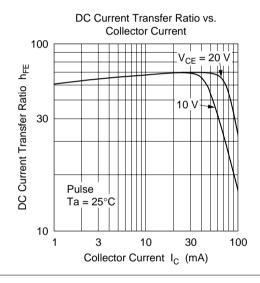
Electrical Characteristics ($Ta = 25^{\circ}C$)

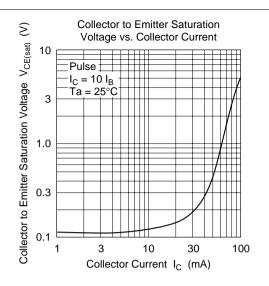
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	300	_	_	V	$I_{c} = 10 \ \mu A, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	300	_	_	V	$I_{C} = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \ \mu\text{A}, \ I_{C} = 0$
Collector cutoff current	I _{CEO}	_	_	1	μA	V _{CE} = 250 V, R _{BE} =
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.5	V	$I_C = 20 \text{ mA}, I_B = 2 \text{ mA}$
DC current transfer ratio	h _{FE}	30	_	200		$V_{CE} = 20 \text{ V}, I_{C} = 20 \text{ mA}$
Gain bandwidth product	f _T	_	80	_	MHz	$V_{CE} = 20 \text{ V}, I_{C} = 20 \text{ mA}$
Collector output capacitance	Cob	_	_	4	pF	$V_{CB} = 20 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

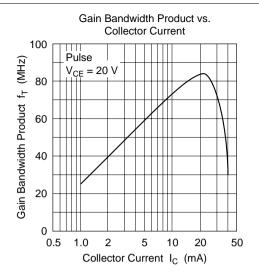


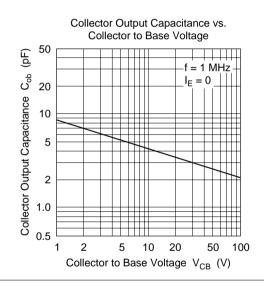




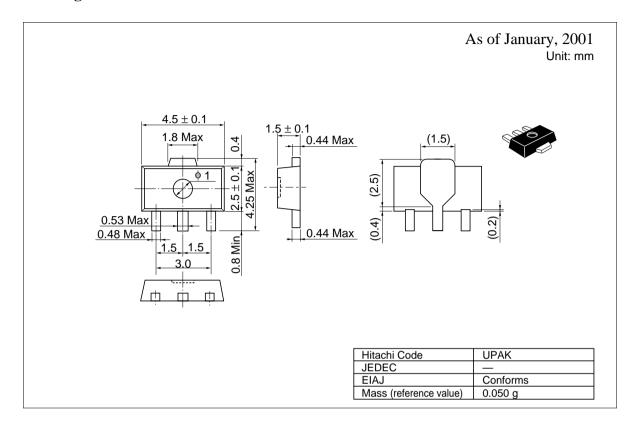








Package Dimensions



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